

## REMARKS

### Rejections Under 35 U.S.C. § 102(b)

Claim 1 stands rejected as anticipated over Myers (U.S. Pat. No. 5,256,487). The Examiner states that Myers discloses the compound of claim 1 at column 15, lines 3-23.

Applicants respectfully disagree. Myers discloses a cyclic silicon-nitrogen monomer. It is significantly different from the compound of the in that Myers' composition comprises N atoms bonded to two silicone atoms (see Myers, Abstract). The compositions noted at column 15, lines 3-23 of Myers do not contain nitrogen atoms. Myers does not teach a composition with a compound containing, for example, Si-Si bonds which is a feature of compositions of the present invention.

Applicants request that the anticipation rejection be withdrawn.

### Rejections Under 35 U.S.C. § 103(a)

Claims 2-4 and 7 stand rejected rejected as obvious over Myers in view of Nakano (U.S. Patent No. 5,840,821). As explained above, Myers does not teach or suggest the compound of claim 1. Nakano, which was cited in the previous Office Action, also does not teach or suggest the compound of claim 1 (see Applicants Response filed February 27, 2006). Accordingly all claim limitations are not taught or suggested, and a *prima facie* case of obviousness has not been established.

Claims 5-6 and 8-10 stand rejected as obvious over Myers, in view of Nakano and further in view of Lukas (U.S. Published Application No. 2004/0096672). Again as noted in Applicant's prior response, Lukas also does not teach or suggest the compound of claim 1. Accordingly, the references alone or combined, do not teach or suggest the limitations of claim 1-10. Applicants request that the rejection be withdrawn.

Applicants also respectfully note for the record that the Examiners remarks regarding the dependent claim limitations are erroneous. Myers does not disclose a CVD (chemical vapor

deposition) method or a liquid phase epitaxy method. Nakano discloses a plasma CVD (chemical vapor deposition) technique (see Nakano et al., U.S. 5,840,821, column 24, line 51), which is significantly different from the present invention which discloses the thermal CVD method (see the description of the present invention, page 9, line 15). Lukas (U.S. 20040096672 A1) does not teach or suggest "vaporizing an organic Si-containing compound and an organic hafnium compound, thermally decomposing the vaporized organic Si-containing compound and the vaporized organic hafnium compound and allowing the decomposed compounds to react with one of NH<sub>3</sub> gas and O<sub>2</sub> gas". Lukas also does not teach or suggest "forming the film is conducted at a temperature not greater than 700°C and the film forming is performed in 5 minutes or less".

In view of the above amendment, applicant believes the pending application is in condition for allowance.

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Respectfully submitted,

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